

R-C Thermal Model Parameters

DESCRIPTION

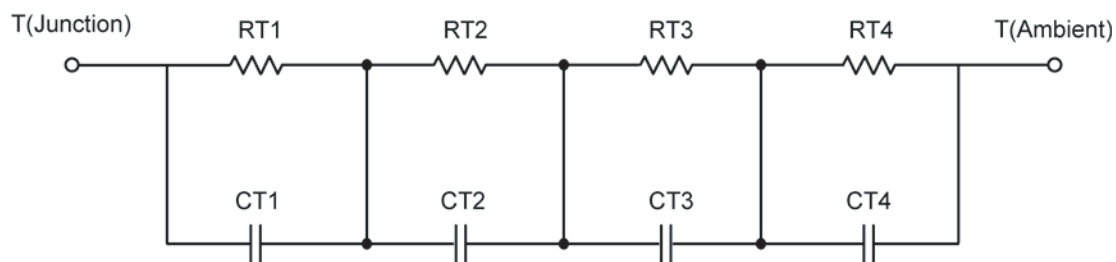
The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

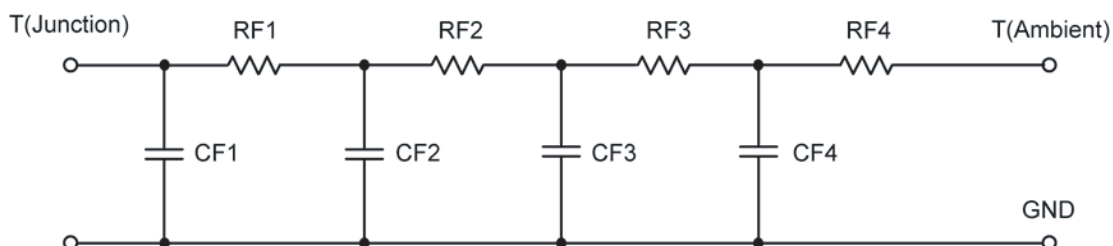
For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	21.6841	N/A	13.9304
RT2	7.0702	N/A	4.7464
RT3	33.4730	N/A	13.4924
RT4	47.0954	N/A	7.8625
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	11.0131 m	N/A	6.4758 m
CT2	746.2615 u	N/A	479.1574 u
CT3	61.2112 m	N/A	49.7764 m
CT4	1.3769	N/A	280.2423 m

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION**R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance ($^{\circ}\text{C}/\text{W}$)			
Junction to	Ambient	Case	Foot
RF1	7.3489	N/A	5.9484
RF2	25.6210	N/A	17.9502
RF3	31.8235	N/A	8.9119
RF4	44.7814	N/A	7.0769
Thermal Capacitance (Joules/ $^{\circ}\text{C}$)			
Junction to	Ambient	Case	Foot
CF1	672.0478 μ	N/A	457.3987 μ
CF2	7.1850 m	N/A	5.6889 m
CF3	48.6044 m	N/A	56.7819 m
CF4	1.3569	N/A	76.8666 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

